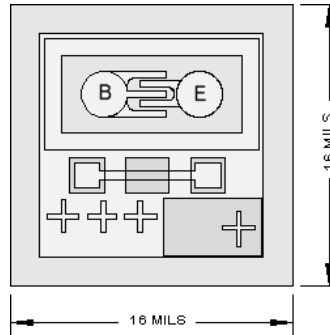


**Chip Type 2C2857**  
**Geometry 0011**  
**Polarity NPN**

**Generic Packaged Part:**  
**2N2857**



[Request Quotation](#)

Chip type **2C2857** by Semicoa Semiconductors provides performance similar to these devices.

**Part Numbers:**

2N2857, 2N2857UB, SD2857, SD2857F, SQ2857, SQ2857F

**Product Summary:**

**APPLICATIONS:** Designed for use in high-gain, low noise amplifier, oscillator, mixer and UHF converters.

**Features:**  $f_t = 1.2 \text{ GHz (typ) at } 5 \text{ mA/6V}$

Mechanical Specifications		
Metallization	Top	Al - 15 kÅ min.
	Backside	Au - 6.5 kÅ nom.
Bonding Pad Size	Emitter	2.3 mils x 2.3 mils
	Base	2.3 mils x 2.3 mils
Die Thickness	8 mils nominal	
Chip Area	16 mils x 16 mils	
Top Surface	Silox Passivated	

Electrical Characteristics				
$T_A = 25^\circ\text{C}$				
Parameter	Test conditions	Min	Max	Unit
$BV_{CEO}$	$I_C = 3.0 \text{ mA}$	15	---	V dc
$BV_{CBO}$	$I_C = 1.0 \mu\text{A}$	30	---	V dc
$BV_{EBO}$	$I_E = 10 \mu\text{A}$	2.5	---	V dc
$I_{CBO}$	$V_{CB} = 15 \text{ V}$	---	0.01	$\mu\text{A dc}$
$h_{FE}$	$I_C = 3.0 \text{ mA dc, } V_{CE} = 1.0 \text{ V}$	30	150	---

*Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width of less than 300  $\mu\text{s}$ , duty cycle less than 2%.*